





# **OUTLINE**

- What is EBL2
- Overview EBL2
- Realization of EBL2
- Differential pumping assembly
- Sample handling in vacuum
- Conclusion





## WHAT IS EBL2

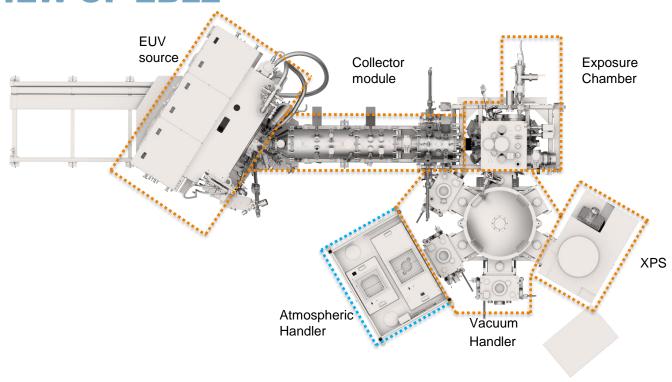
- > EBL2 is not a setup for producing semiconductor devices
- The experiments for which EBL2 is intended are:
  - Accelerated lifetime tests for:
    - > EUV Mirrors
    - EUV Reticles and pellicles
    - Materials used in EUV lithography
  - This kind of research is needed due to the harsh EUV environment, and
  - EUV lithography is coming to market
- EBL2 is able manipulate and to illuminate EUV reticles with scanner compatibility



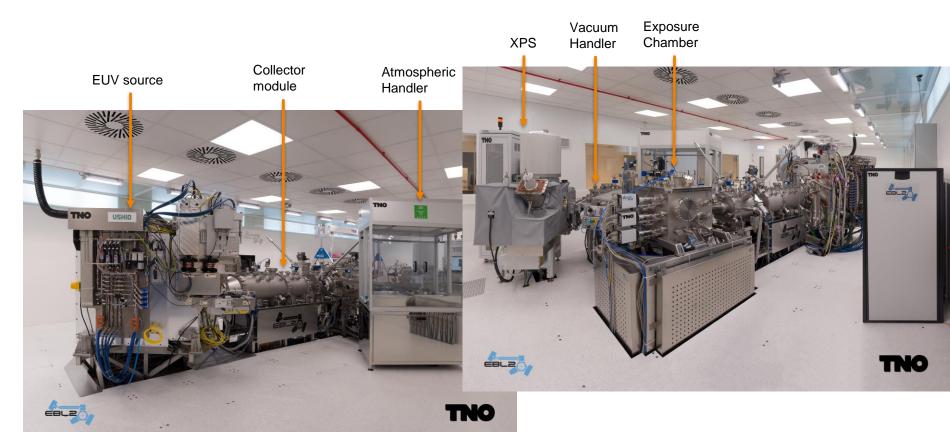




# **OVERVIEW OF EBL2**



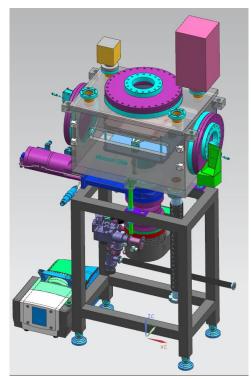


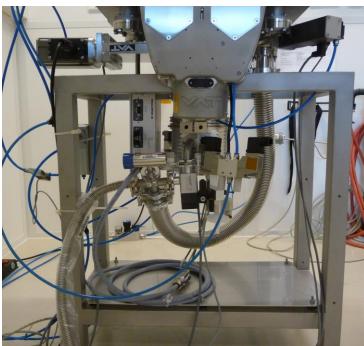


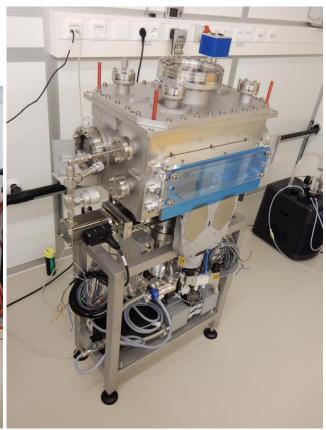




# **REALIZATION: LOAD LOCK**





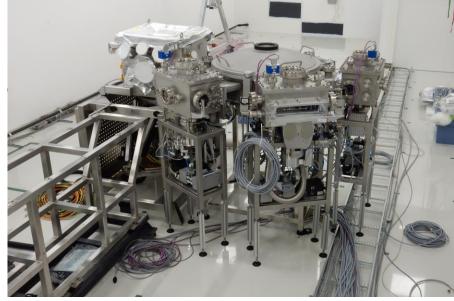






# REALIZATION: EXPOSURE CHAMBER AND VACUUM HANDLER





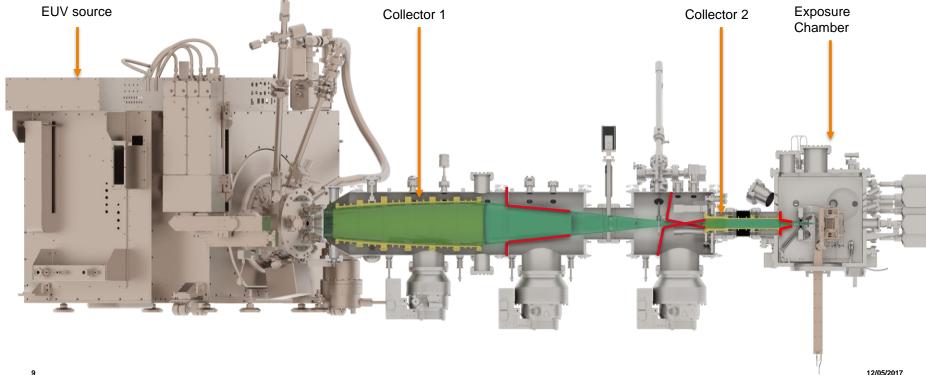




- Problem statement:
  - The gas environments from both the exposure chamber and the source may not influence each other
- > Filters or windows are not an option, so another solution had to be found and is implemented

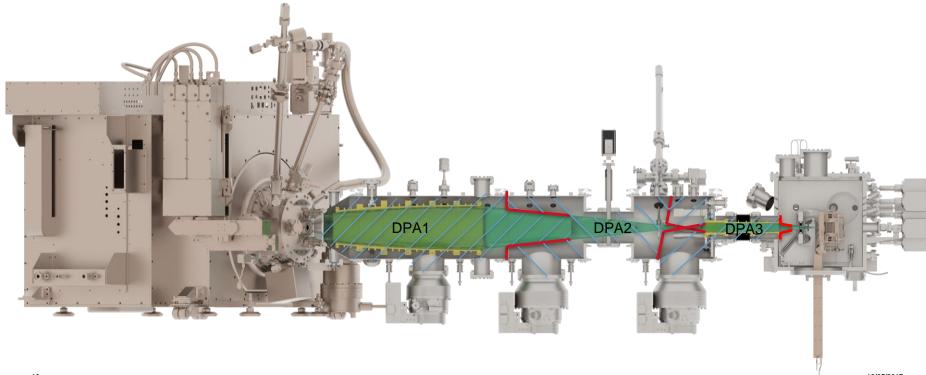








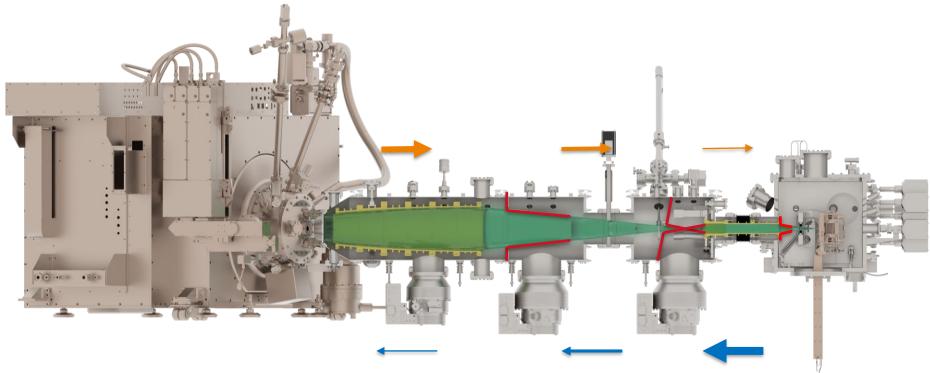




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# **MOTION IN VACUUM**

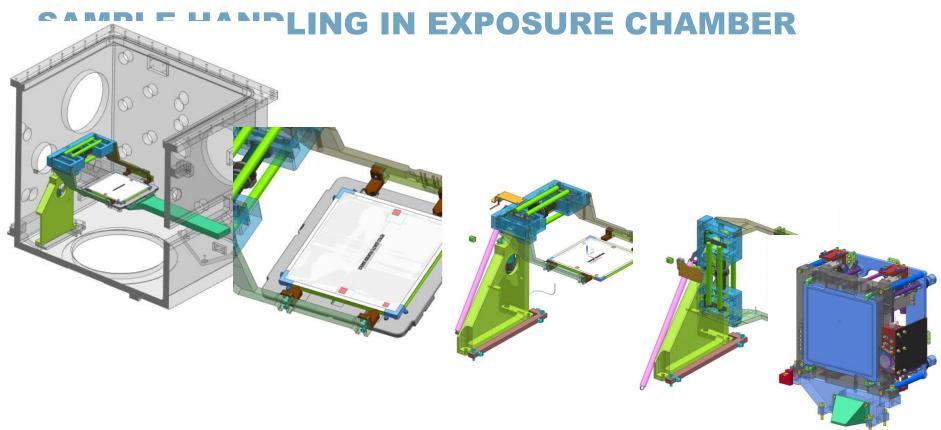
Dummy reticle on base plate



End effector of vacuum robot



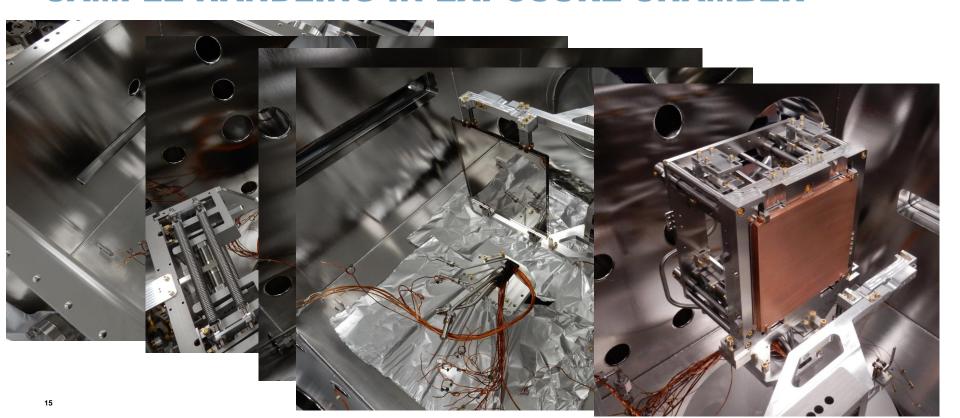








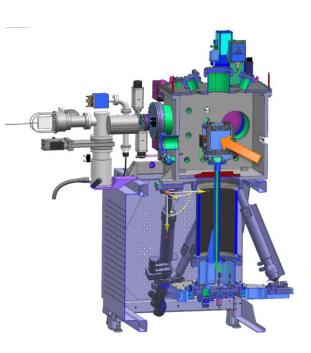
# SAMPLE HANDLING IN EXPOSURE CHAMBER

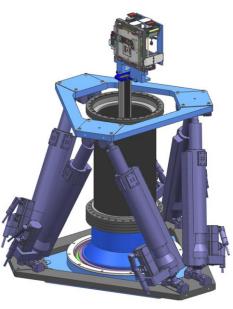




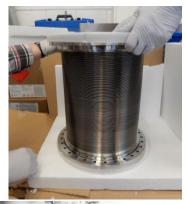


# **HEXAPOD**







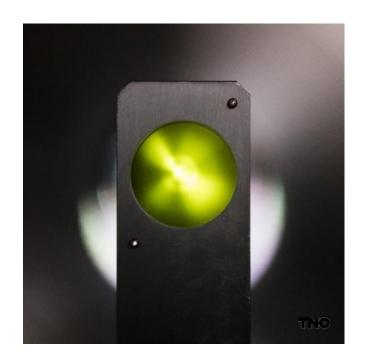








# FIRST LIGHT (DEC 2016)





Focal point





### CONCLUSION

#### > www.tno.nl/EBL2

From end of Q3 2017, EBL2 will be an unique facility, accessible for semiconductor industry, that enables EUV lifetime research with:

- EUV scanner relevant conditions
- Up to EUV mask sample size
- High flexibility in environmental conditions
- Automated reticle handling
- Real time, in-situ data on sample status
- In vacuum surface analysis

#### Acknowledgements

- SeNaTe, E450LMDAP, NanoLabNL (Sponsors)
- USHIO and ASYS (Technology Partners)
- Zeiss SMT (Discussions)





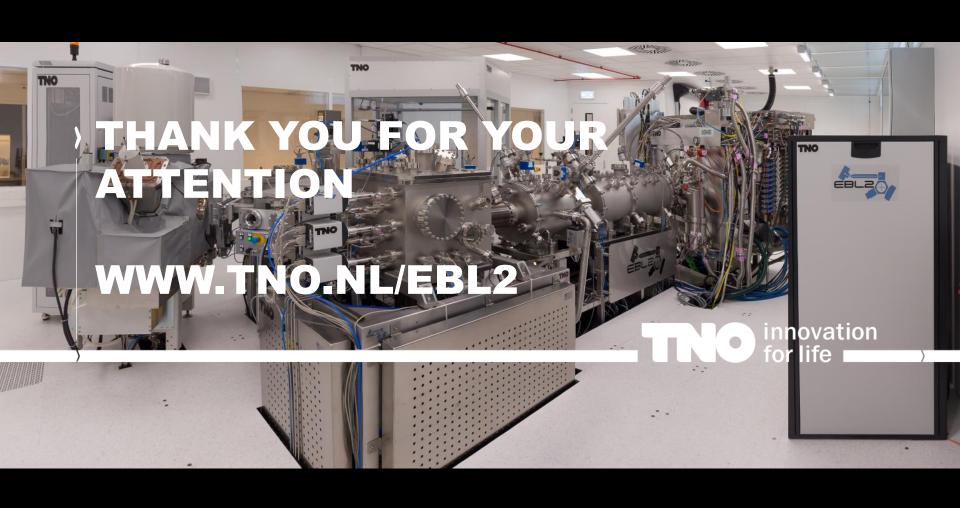








We make it visible.

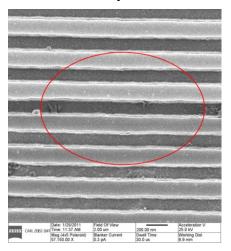


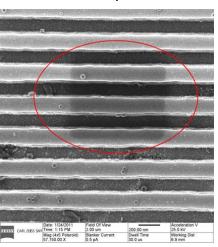




# **WHAT IS EUVL**

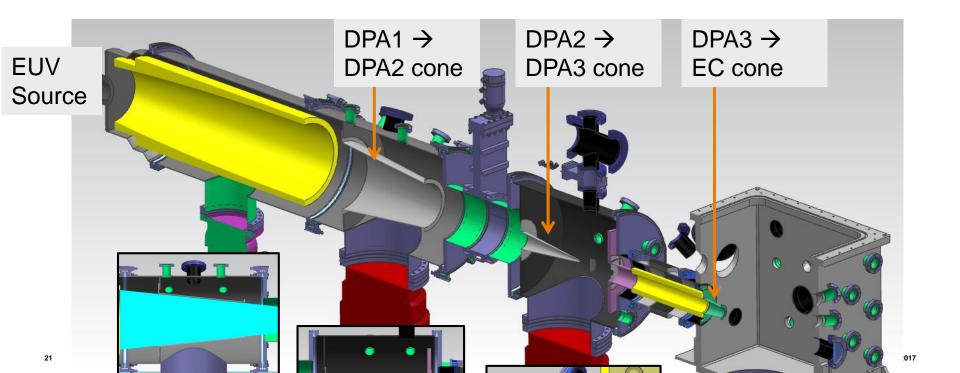
- > EUVL uses λ 13,5 nm, generated with a Sn fuelled plasma
- An EUV stepper needs to be an ultra clean vacuum (UCV) system
  - Very sensitive for molecular and particle contamination















# **XPS AT TNO**





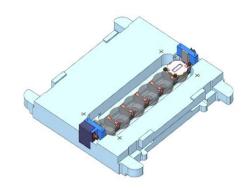


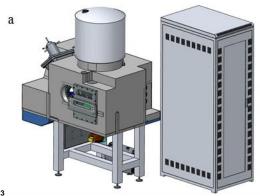


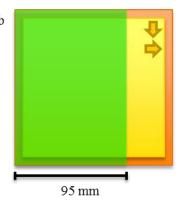


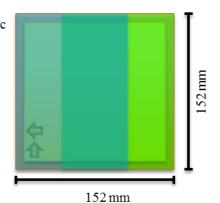
# **XPS**

- Modified Kratos Axis Nova system
  - Handling reticles:100% coverage with one rotation
  - Batch processing of multiple samples
  - Angle resolved measurement for better surface sensitivity
  - Automated movement to predefined position (defect mapping)





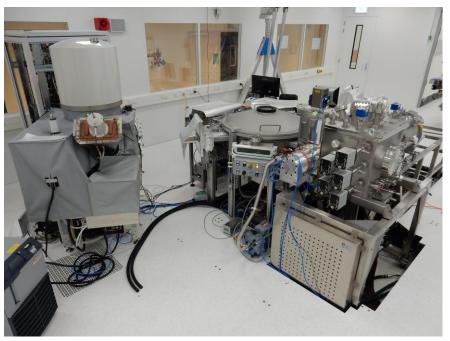








# **REALISATION**







# **COLLECTOR MODULE**



